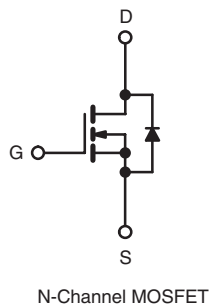
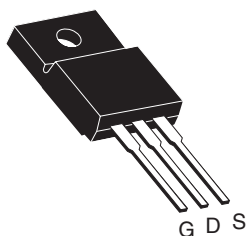


## Power MOSFET

### PRODUCT SUMMARY

$V_{DS}$ (V)	600	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$	4.4
$Q_g$ (Max.) (nC)	18	
$Q_{gs}$ (nC)	3.0	
$Q_{gd}$ (nC)	8.9	
Configuration	Single	

TO-220 FULLPAK



### FEATURES

- Isolated Package
- High Voltage Isolation = 2.5 kV<sub>RMS</sub> (t = 60 s; f = 60 Hz)
- Sink to Lead Creepage Distance = 4.8 mm
- Dynamic dV/dt Rating
- Low Thermal Resistance
- Lead (Pb)-free Available



Available  
**RoHS\***  
COMPLIANT

### DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 FULLPAK eliminates the need for additional insulating hardware in commercial-industrial applications. The molding compound used provides a high isolation capability and a low thermal resistance between the tab and external heatsink. The isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The FULLPAK is mounted to a heatsink using a single clip or by a single screw fixing.

### ORDERING INFORMATION

Package	TO-220 FULLPAK
Lead (Pb)-free	IRFIBC20GPbF SiHFIBC20G-E3
SnPb	IRFIBC20G SiHFIBC20G

### ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V <sub>DS</sub>	600	V
Gate-Source Voltage			V <sub>GS</sub>	± 20	
Continuous Drain Current	V <sub>GS</sub> at 10 V	T <sub>C</sub> = 25 °C	I <sub>D</sub>	1.7	A
		T <sub>C</sub> = 100 °C		1.1	
Pulsed Drain Current <sup>a</sup>			I <sub>DM</sub>	6.8	
Linear Derating Factor				0.24	W/°C
Single Pulse Avalanche Energy <sup>b</sup>			E <sub>AS</sub>	84	mJ
Repetitive Avalanche Current <sup>a</sup>			I <sub>AR</sub>	1.7	A
Repetitive Avalanche Energy <sup>a</sup>			E <sub>AR</sub>	3.0	mJ
Maximum Power Dissipation	T <sub>C</sub> = 25 °C		P <sub>D</sub>	30	W
Peak Diode Recovery dV/dt <sup>c</sup>			dV/dt	3.0	V/ns
Operating Junction and Storage Temperature Range			T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s			300 <sup>d</sup>	
Mounting Torque	6-32 or M3 screw			10	lbf · in
				1.1	N · m

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50\text{ V}$ , starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 53\text{ mH}$ ,  $R_G = 25\text{ }\Omega$ ,  $I_{AS} = 1.7\text{ A}$  (see fig. 12).
- $I_{SP} \leq 2.2\text{ A}$ ,  $dI/dt \leq 40\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150\text{ }^\circ\text{C}$ .
- 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

**THERMAL RESISTANCE RATINGS**

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	65	°C/W
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	4.1	

**SPECIFICATIONS**  $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA		600	-	-	V
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	Reference to 25 °C, I <sub>D</sub> = 1 mA		-	0.88	-	V/°C
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA		2.0	-	4.0	V
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V		-	-	100	μA
		V <sub>DS</sub> = 480 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C		-	-	500	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 1.0 A <sup>b</sup>	-	-	4.4	Ω
Forward Transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 1.0 A <sup>b</sup>		1.4	-	-	S
Dynamic							
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1.0 MHz, see fig. 5		-	350	-	pF
Output Capacitance	C <sub>oss</sub>			-	48	-	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	8.6	-	
Drain to Sink Capacitance	C	f = 1.0 MHz		-	12	-	
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 2.0 A, V <sub>DS</sub> = 360 V, see fig. 6 and 13 <sup>b</sup>	-	-	18	nC
Gate-Source Charge	Q <sub>gs</sub>			-	-	3.0	
Gate-Drain Charge	Q <sub>gd</sub>			-	-	8.9	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 300 V, I <sub>D</sub> = 2.0 A, R <sub>G</sub> = 18Ω, R <sub>D</sub> = 150 Ω, see fig. 10 <sup>b</sup>		-	10	-	ns
Rise Time	t <sub>r</sub>			-	23	-	
Turn-Off Delay Time	t <sub>d(off)</sub>			-	30	-	
Fall Time	t <sub>f</sub>			-	25	-	
Internal Drain Inductance	L <sub>D</sub>	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	nH
Internal Source Inductance	L <sub>S</sub>			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode		-	-	1.7	A
Pulsed Diode Forward Current <sup>a</sup>	I <sub>SM</sub>			-	-	6.8	
Body Diode Voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 1.7 A, V <sub>GS</sub> = 0 V <sup>b</sup>		-	-	1.6	V
Body Diode Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = 2.0 A, dI/dt = 100 A/μs <sup>b</sup>		-	290	580	ns
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			-	0.65	1.3	μC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and L <sub>D</sub> )					

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).  
b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

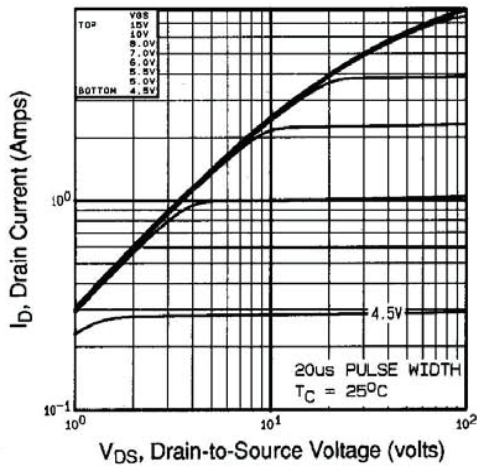


Fig. 1 - Typical Output Characteristics,  $T_C = 25^\circ\text{C}$

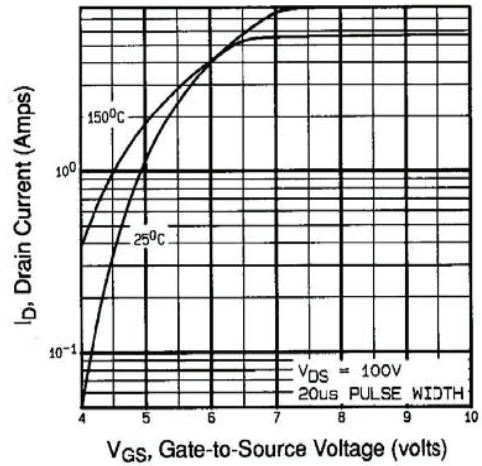


Fig. 3 - Typical Transfer Characteristics

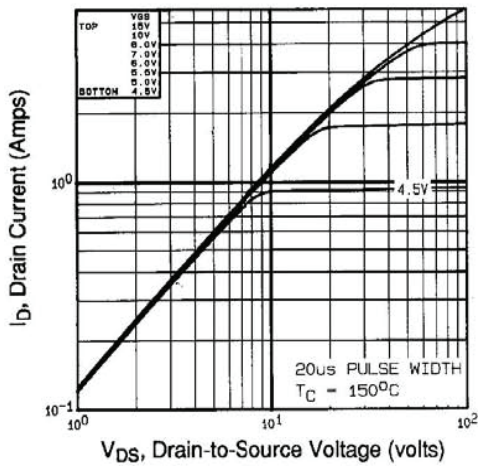


Fig. 2 - Typical Output Characteristics,  $T_C = 150^\circ\text{C}$

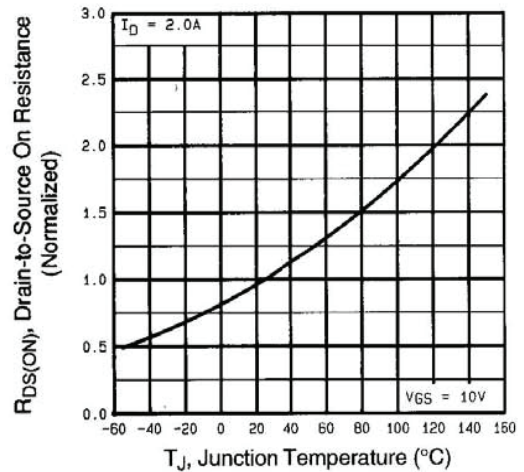


Fig. 4 - Normalized On-Resistance vs. Temperature

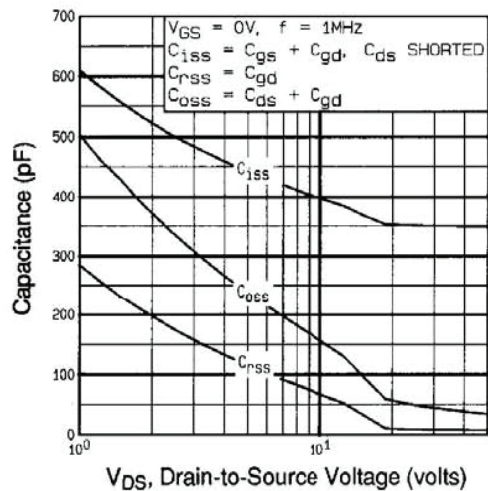


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

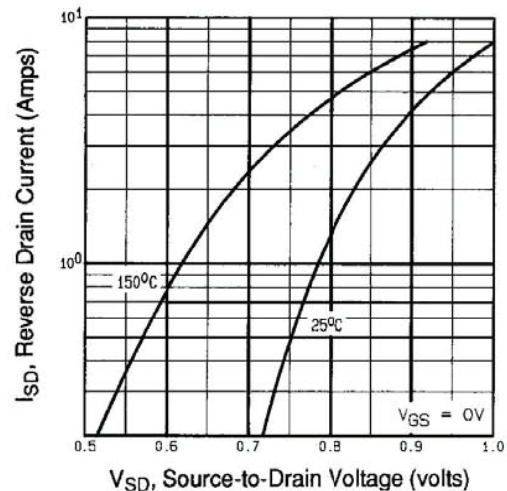


Fig. 7 - Typical Source-Drain Diode Forward Voltage

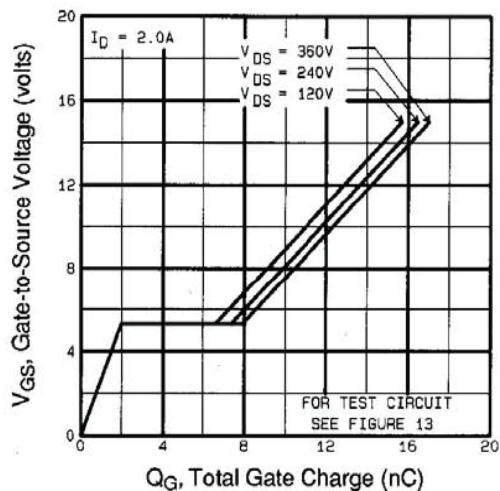


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

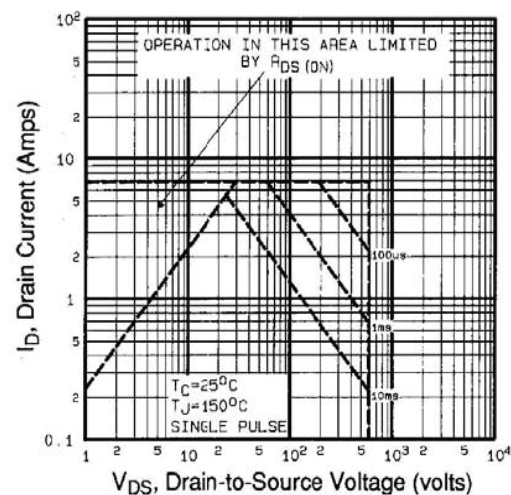


Fig. 8 - Maximum Safe Operating Area

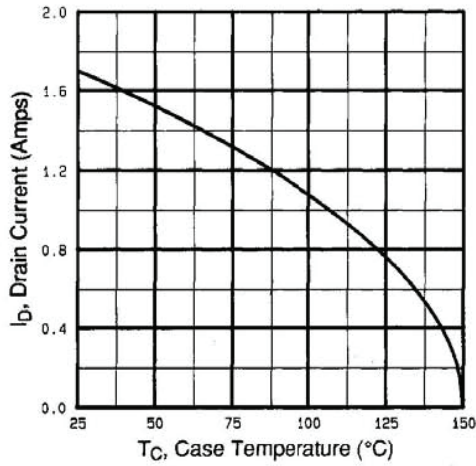


Fig. 9 - Maximum Drain Current vs. Case Temperature



Fig. 10a - Switching Time Test Circuit

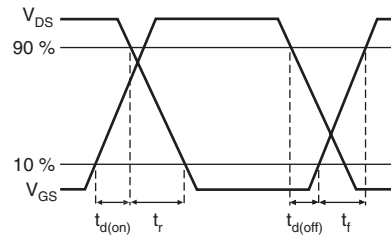


Fig. 10b - Switching Time Waveforms

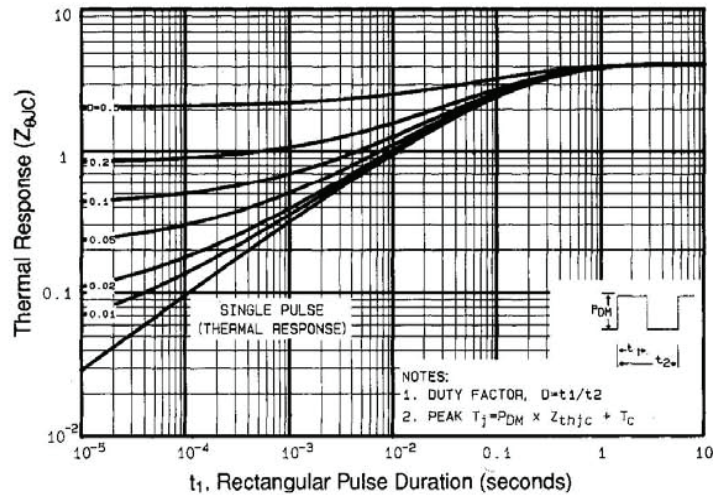


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

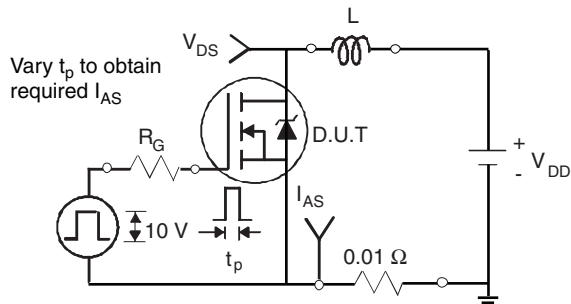


Fig. 12a - Unclamped Inductive Test Circuit

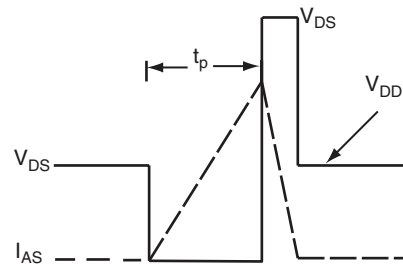


Fig. 12b - Unclamped Inductive Waveforms

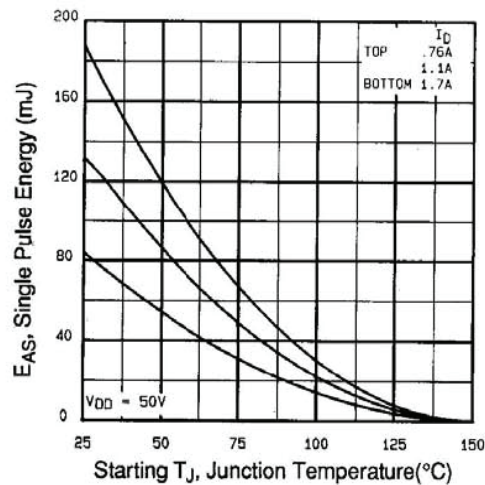


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

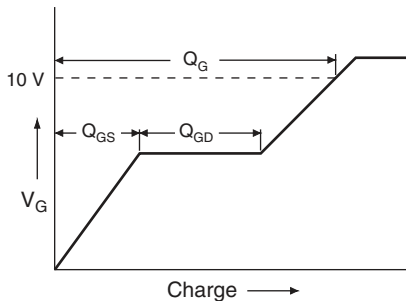


Fig. 13a - Basic Gate Charge Waveform

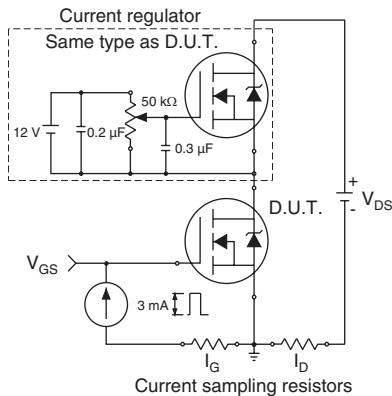


Fig. 13b - Gate Charge Test Circuit



① Driver gate drive

P.W. Period  $D = \frac{\text{P.W.}}{\text{Period}}$

$V_{GS} = 10 \text{ V}^*$

② D.U.T.  $I_{SD}$  waveform

Reverse recovery current

Body diode forward current

$di/dt$

③ D.U.T.  $V_{DS}$  waveform

Diode recovery  $dV/dt$

$V_{DD}$

Body diode forward drop

④ Inductor current

Ripple  $\leq 5\%$

$I_{SD}$

\*  $V_{GS} = 5 \text{ V}$  for logic level devices

**Fig. 14 - For N-Channel**

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